

### Three Phase Rectifier Bridge with IGBT and Fast Recovery Diode for Braking System

### PSDI 33/06

$I_{C25} = 44 \text{ A}$   
 $V_{CES} = 600 \text{ V}$   
 $I_{FAV25} = 18 \text{ A}$   
 $V_{RRM} = 1200 \text{ V}$

Preliminary Data Sheet

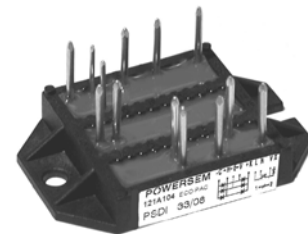
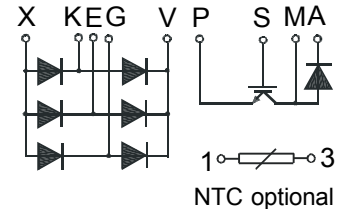
#### IGBT

Symbol	Test Conditions	Maximum Ratings
$V_{CES}$	$T_{VJ} = 25 \text{ }^\circ\text{C to } 150 \text{ }^\circ\text{C}$	600 V
$V_{GES}$	continuous	$\pm 20$ V
$I_{C25}$	$T_C = 25 \text{ }^\circ\text{C}$	44 A
$I_{C80}$	$T_S = 80 \text{ }^\circ\text{C}$	30 A
<b>RBSOA</b>	$V_{CE} = 600 \text{ V}, R_G = 10 \text{ } \Omega, T_{VJ} = 125 \text{ }^\circ\text{C}$ clamped inductive load, $L = 100 \text{ } \mu\text{H}$	$I_{CM} = 100$ A $V_{CEK} \leq V_{CES}$
$t_{SC}$	$V_{CE} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}, R_G = 10 \text{ } \Omega,$ $T_{VJ} = 125 \text{ }^\circ\text{C}, \text{ non-repetitive}$	10 $\mu\text{s}$

Symbol	Test Conditions	Characteristic Values
$T_{VJ} = 25 \text{ }^\circ\text{C}, \text{ unless otherwise specified}$		
$V_{CE(sat)}$	$V_{GE} = 15 \text{ V}, I_C = 10 \text{ A}, T_{VJ} = 25 \text{ }^\circ\text{C}$	max. 1.8 V
$V_{CE(sat)}$	$V_{GE} = 15 \text{ V}, I_C = 10 \text{ A}, T_{VJ} = 25 \text{ }^\circ\text{C}$	typ. 1.5 V
$V_{CE(sat)}$	$T_{VJ} = 125 \text{ }^\circ\text{C}$	typ. 1.6 V
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1 \text{ mA}$	min. 3 V
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1 \text{ mA}$	max. 5 V
$I_{CES}$	$V_{CE} = V_{CES}, V_{GE} = 0 \text{ V}, T_{VJ} = 25 \text{ }^\circ\text{C}$	max. 0.04 mA
$I_{CES}$	$T_{VJ} = 125 \text{ }^\circ\text{C}$	typ. 1 mA
$I_{GES}$	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$	max. 100 nA
$t_{d(on)}$	$\left. \begin{array}{l} \text{inductive load, } T_{VJ} = 125 \text{ }^\circ\text{C} \\ V_{CE} = 400 \text{ V}, I_C = 10 \text{ A} \\ V_{GE} = \pm 15 \text{ V}, R_G = 10 \text{ } \Omega \end{array} \right\}$	typ. 31 ns
$t_r$		typ. 50 ns
$t_{d(off)}$		typ. 291 ns
$t_f$		typ. 70 ns
$E_{on}$		typ. 0.60 mJ
$E_{off}$	typ. 0.31 mJ	
$C_{ies}$	$V_{CE} = 25 \text{ V}, f = 1 \text{ MHz}, V_{GE} = 0 \text{ V}$	typ. 1600 pF
$Q_{Gon}$	$V_{CE} = 480 \text{ V}, I_C = 10 \text{ A}, V_{GE} = 15 \text{ V}$	typ. 140 nC
$R_{thJC}$		max. 0.96 K/W
$R_{thJH}$		max. tbd K/W

#### Module

Symbol	Test Conditions	Maximum Ratings
$T_{VJ}$		-40...+150 $^\circ\text{C}$
$T_{JM}$		150 $^\circ\text{C}$
$T_{stg}$		-40...+150 $^\circ\text{C}$
$V_{isol}$	50/60 Hz $t = 1 \text{ min}$	3000 V~
	lisol $\leq 1 \text{ mA}$ $t = 1 \text{ s}$	3600 V~
$M_d$	Mounting torque (M 4)	1.5-2.0 Nm
<b>Weight</b>	typ.	24 g



#### Features

- High level of integration - only one power semiconductor module required for the whole braking system module
- Isolation voltage 3600 V~
- Planar glass passivated chips
- Ultrafast freewheel diode
- Leads suitable for PC board soldering
- Thermistor (optional)

#### Applications

- Drive inverters with brake system

#### Advantages

- Easy to mount with two screws
- Space and weight savings
- high temperature and power cycling capability
- Small and light weight
- 2 functions in one package

**Caution:** These Devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

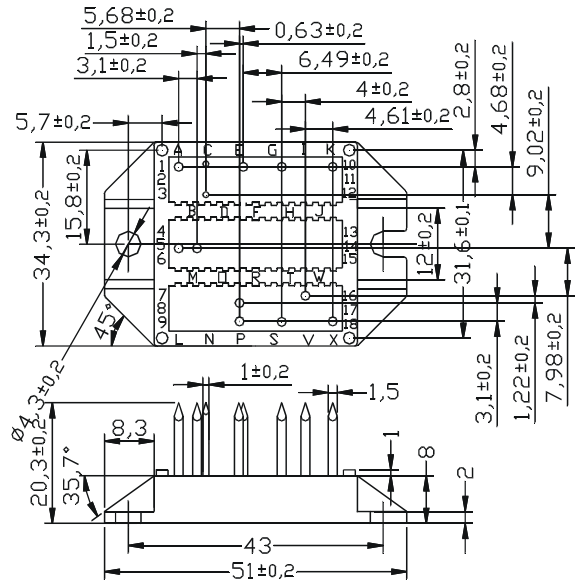
Data according to IEC 60747 refer to a single diode unless otherwise stated

## Fast Recovery Diode

Symbol	Test Conditions	Maximum Ratings	
$V_{RRM}$	$T_{VJ} = 25\text{ °C to }150\text{ °C}$	600	V
$I_{F25}$	$T_C = 25\text{ °C}$	30	A
$I_{F80}$	$T_C = 80\text{ °C}$	19	A

Symbol	Test Conditions	Characteristic Values			
$T_{VJ} = 25\text{ °C}$ , unless otherwise specified					
$V_F$	$I_F = 10\text{ A}$ , $T_{VJ} = 25\text{ °C}$	$T_{VJ} = 25\text{ °C}$	max.	3.2	V
		$T_{VJ} = 25\text{ °C}$	typ.	2.2	V
		$T_{VJ} = 125\text{ °C}$	max.	2.4	V
$I_R$	$V_R = V_{RRM}$ , $T_{VJ} = 25\text{ °C}$	$T_{VJ} = 25\text{ °C}$	max.	0.1	mA
		$T_{VJ} = 125\text{ °C}$	typ.	0.1	mA
$I_{RM}$	$I_F = 10\text{ A}$ , $di_F/dt = -400\text{ A}/\mu\text{s}$ , $T_{VJ} = 125\text{ °C}$		tbd	A	
$t_{tr}$	$V_R = 400\text{ V}$		tbd	ns	
$R_{thJC}$		max.	1.15	K/W	
$R_{thJH}$	with heat transfer paste		tbd	K/W	

**Package style and outline**  
Dimensions in mm (1mm = 0.0394")



## Rectifier Diodes

Symbol	Test Conditions	Maximum Ratings	
$V_{RRM}$		1200	V
$I_{FAV25}$	$T_C = 25\text{ °C}$ , sine 180 °	41	A
$I_{FAV80}$	$T_C = 80\text{ °C}$ , sine 180 °	28	A
$I_{FSM}$	$T_{VJ} = 25\text{ °C}$ , $T = 10\text{ ms}$ (50Hz)	75	A

Symbol	Test Conditions	Characteristic Values			
$T_{VJ} = 25\text{ °C}$ , unless otherwise specified					
$V_F$	$I_F = 10\text{ A}$ , $T_{VJ} = 25\text{ °C}$	$T_{VJ} = 25\text{ °C}$	max.	1.8	V
		$T_{VJ} = 25\text{ °C}$	typ.	1.4	V
		$T_{VJ} = 125\text{ °C}$	typ.	1.6	V
$I_R$	$V_R = V_{RRM}$ , $T_{VJ} = 25\text{ °C}$	$T_{VJ} = 25\text{ °C}$	max.	0.05	mA
		$T_{VJ} = 125\text{ °C}$	typ.	0.5	mA
$t_{tr}$	$V_R = 100\text{ V}$ , $I_F = 10\text{ A}$ , $-di/dt = 5\text{ A}/\mu\text{s}$	typ.	1	$\mu\text{s}$	
$R_{thJC}$	per diode	max.	2.5	K/W	
$R_{thJH}$	with heat transfer paste		tbd	K/W	

## Module

Symbol	Test Conditions	Characteristic Values	
$d_s$	Creeping distance on surface	11.2	mm
$d_A$	Creeping distance in air	5	mm
$a$	Max. allowable acceleration	50	m/s <sup>2</sup>
$R_{25}^*$	NTC @ 25 °C	470.000	$\Omega$

\*NTC will be changed in future to 5.000  $\Omega$ .